Unit: mm

TOSHIBA Insulated Gate bipolar Transistor Silicon N Channel IGBT

**Preliminary** 

GT40Q322

### Voltage Resonance Inverter Switching Application

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- Enhancement-mode
- High speed :  $t_f = 0.14 \mu s$  (typ.) (IC = 40A)
- FRD included between emitter and collector
- The 4th generation
- TO-3P(N) (Toshiba package name)

#### **Maximum Ratings (Ta = 25°C)**

Characteris	stics	Symbol	Rating	Unit	
Collector-emitter voltage		$V_{CES}$	1200	V	
Gate-emitter voltage		V <sub>GES</sub>	±25	V	
Continuous collector current	@ Tc = 100°C	I <sub>C</sub>	20	А	
	@ Tc = 25°C	iC	39		
Pulsed collector curren	ıt	I <sub>CP</sub>	80	Α	
Diode forward current	DC	l <sub>F</sub>	10	А	
Diode forward current	Pulsed	I <sub>FP</sub>	80		
Collector power dissipation	@ Tc = 100°C	Pc	80	W	
	@ Tc = 25°C	FC	200	W	
Junction temperature		Tj	150	°C	
Storage temperature ra	ange	T <sub>stg</sub>	−55 to 150	°C	

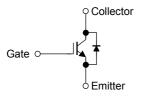
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Weight: 4.6 g (typ.)

#### **Thermal Characteristics**

Characteristics	Symbol	Max	Unit
Thermal resistance (IGBT)	R <sub>th (j-c)</sub>	0.625	°C/W
Thermal resistance (diode)	R <sub>th (j-c)</sub>	1.79	°C/W

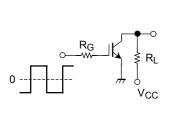
### **Equivalent Circuit**

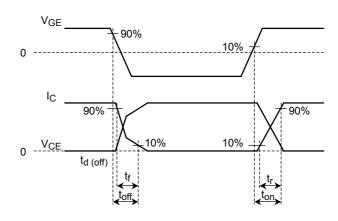


## Electrical Characteristics (Ta = 25°C)

	Characteristics  Gate leakage current  Collector cut-off current  www.datas Gaté-emitter cut-off voltage		Symbol	Test Condition	Min	Тур.	Max	Unit
			I <sub>GES</sub>	V <sub>GE</sub> = ±25 V, V <sub>CE</sub> = 0	_	_	±500	nA
			I <sub>CES</sub>	V <sub>CE</sub> = 1200 V, V <sub>GE</sub> = 0	_	_	5.0	mA
www.datas			V <sub>GE</sub> (OFF)	I <sub>C</sub> = 40 mA, V <sub>CE</sub> = 5 V	4.0	_	7.0	V
	Collector-emitter saturation voltage		V <sub>CE</sub> (sat)	I <sub>C</sub> = 40 A, V <sub>GE</sub> = 15 V	_	3.0	3.7	V
	Input capacitance		C <sub>ies</sub>	V <sub>CE</sub> = 10 V, V <sub>GE</sub> = 0, f = 1 MHz	_	5550	_	pF
	Switching time	Rise time	t <sub>r</sub>	Resistive Load $V_{CC} = 600 \text{ V, } I_{C} = 40 \text{ A}$ $V_{GG} = \pm 15 \text{ V, } R_{G} = 39 \Omega$	_	0.18	_	μs
		Turn-on time	t <sub>on</sub>		_	0.26	_	
		Fall time	t <sub>f</sub>		_	0.14	0.21	
		Turn-off time	t <sub>off</sub>	(Note 1)	_	0.43	_	
	Diode forward voltage  Reverse recovery time		V <sub>F</sub>	I <sub>F</sub> = 10 A, V <sub>GE</sub> = 0	_	_	2.0	V
			t <sub>rr</sub>	I <sub>F</sub> = 10 A, di/dt = -20 A/μs	_	0.6	_	μs

Note 1: Switching time measurement circuit and input/output waveforms





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